

MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

Product data sheet

www.msksemi.com

VOLTAGE RANGE

50 to 600 Volts

CURRENT

3.0 Amperes



SMB

FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Low forward voltage drop

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.093 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature unless otherwise specified.
Single phase half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

P/N(MARK)	ES3AB	ES3BB	ES3CB	ES3DB	ES3EB	ES3GB	ES3JB	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	150	200	300	400	600	V
Maximum RMS Voltage	35	70	105	140	210	280	420	V
Maximum DC Blocking Voltage	50	100	150	200	300	400	600	V
Maximum Average Forward Rectified Current .375"(9.5mm) Lead Length at Ta=55°C	3.0							A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	80							A
Maximum Instantaneous Forward Voltage at 3.0A	1.0				1.4	1.7		V
Maximum DC Reverse Current Ta=25°C	5.0							uA
at Rated DC Blocking Voltage Ta=100°C	50							uA
Maximum Reverse Recovery Time (Note 1)	35							nS
Typical Junction Capacitance (Note 2)	60							pF
Operating and Storage Temperature Range Tj, Tstg	-65 — +150							°C

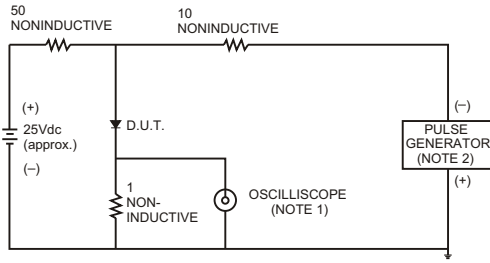
NOTES:

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

RATING AND CHARACTERISTIC CURVES (ES3AB THRU ES3JB)

FIG.1- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC

FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

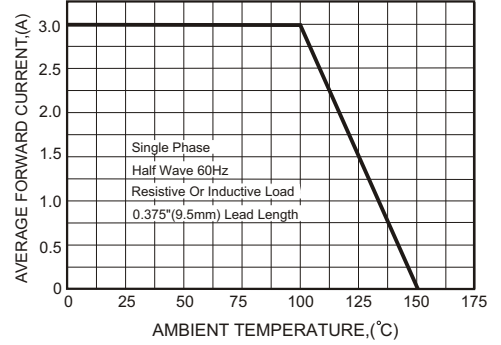
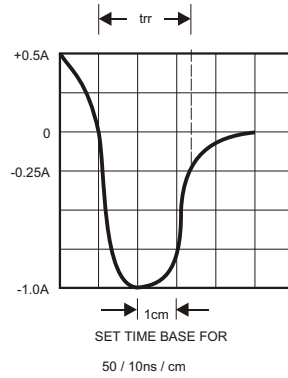


FIG.3-TYPICAL FORWARD CHARACTERISTICS

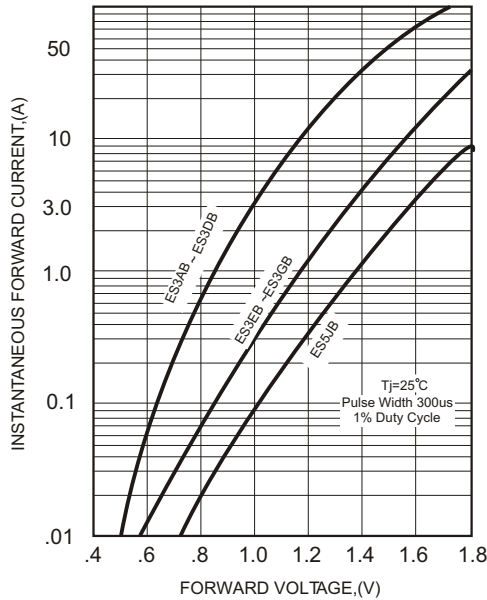


FIG.4-TYPICAL REVERSE CHARACTERISTICS

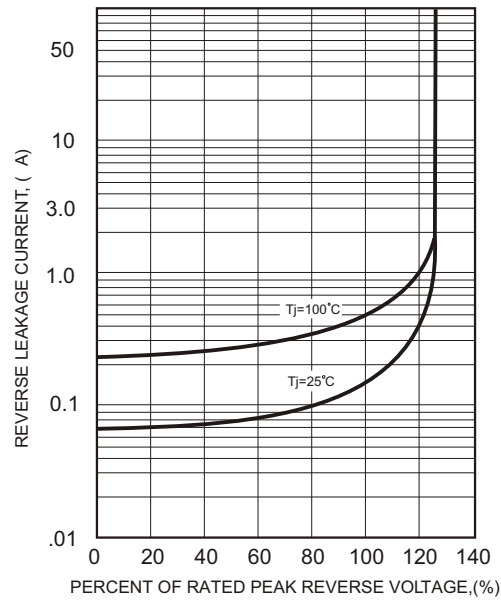


FIG.5-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

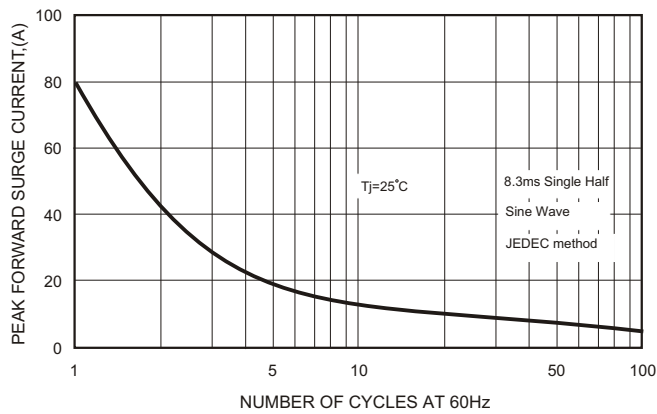
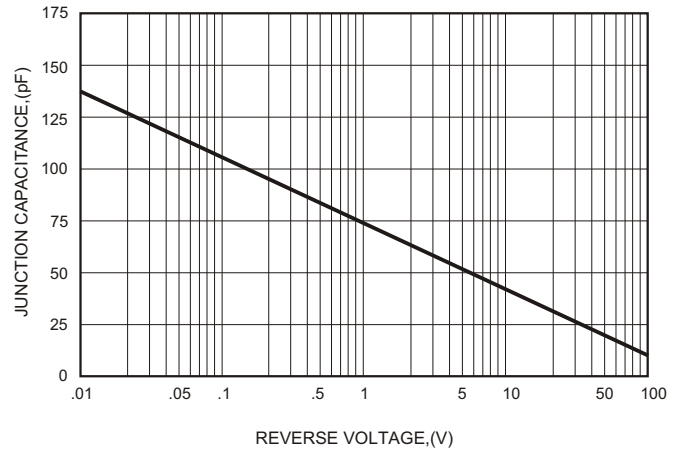
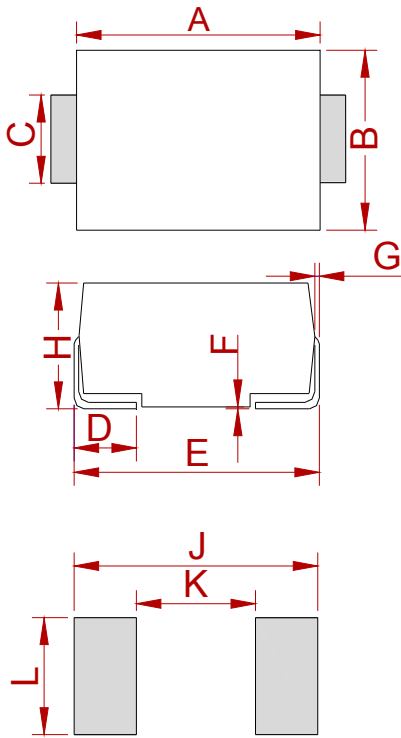


FIG.6-TYPICAL JUNCTION CAPACITANCE



PACKAGE MECHANICAL DATA



DO-214AA (SMB)

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.25	4.75	0.167	0.187
B	3.30	3.94	0.130	0.155
C	1.85	2.21	0.073	0.087
D	0.76	1.52	0.030	0.060
E	5.08	5.59	0.200	0.220
F	0.051	0.203	0.002	0.008
G	0.15	0.31	0.006	0.012
H	2.11	2.44	0.083	0.096
J	6.80		0.270	
K		2.60		0.100
L	2.40		0.090	

REEL SPECIFICATION

P/N	PKG	QTY
ES3AB THRU ES3JB	SMB	3000

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